

Abstract of the Disclosure:

In an integrated circuit configuration, above a first
conductive structure which is embedded in a first insulating
layer there are arranged a first barrier layer and a second
5 insulating layer, in which a contact hole is provided which
reaches down to the first conductive structure. Above the
first barrier layer, the side walls of the contact hole are
provided with spacers which act as a diffusion barrier and
which reach down to the surface of the first barrier layer. A
10 second conductive structure is arranged in the contact hole.
The second conductive structure is conductively connected to
the first conductive structure. During the production of the
contact hole, the spacers prevent deposition of material from
the first conductive structure on the surface of the second
15 insulating layer.